



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: INOUE et al.
Serial No.: 09/698,185
Filed: October 30, 2000
For: SEMICONDUCTOR DEVICE AND METHOD FOR
MANUFACTURING THE SAME
Group: 2827
Examiner: L. Thai

SUPPLEMENTAL AMENDMENT

Assistant Commissioner
for Patents
Washington, D.C. 20231

March 19, 2003

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Sir:

In supplement to the Amendment filed on March 17, 2003, please further
amend the above-identified application as follows:

In the Specification:

Page 16, paragraph beginning at line 11, has been rewritten as indicated
below:

In Fig. 1, a film appears 50 micrometers thick at a horizontal distance
of 500 micrometers from one edge of the stress relaxation layer 5. Hence, the
average gradient is 10%. The redistributing wire 4 is made of an electrical conductor
such as copper. The redistributing wire 4 connects the aluminum pad 7 to a
protrusive electrode and a bump pad 3 on a surface of the stress relaxation layer 5.
A gold plating 2 for preventing the bump pad 3 from being oxidized may be provided
on the bump pad 3. While a dicing area 24 is provided for dicing the wafer 9 having